

**5.6 Watt 3.5GHz Packaged HPA**

**TGA2925-SG**



**Key Features**

- 3.5 GHz Application Frequency Range
- 11 dB Nominal Gain
- 2.5%EVM @29dBm OFDM signal at 3.5GHz
- 37.5 dBm Nominal Psat
- Internally Partially Matched
- IMD3 -50 dBc @ 24 dBm SCL, Typical
- Bias Conditions: 8 V @ 0.75 A (Quiescent)
- 0.5 μm HFET Technology
- 2 lead Cu-alloy base package

**Primary Applications**

- 802.16 and WiMax
- S-Band Power Amplifiers

**Product Description**

The TGA2925-SG HPA provides 11 dB of gain, 5.6 W of output power at 3.5 GHz and 2.5% EVM at 29 dBm output power. The device is ideally suited for high linearity, high power wireless data applications such as 802.16 and WiMax. The package has a high thermal conductivity copper alloy base. Internal partial matching simplifies system board layout by requiring a minimum of external components.

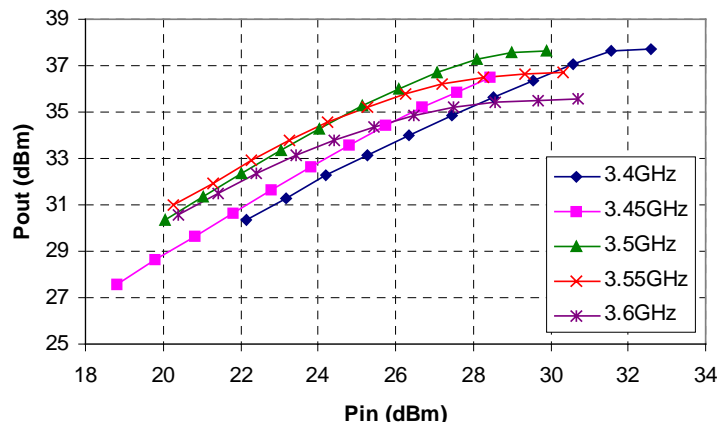
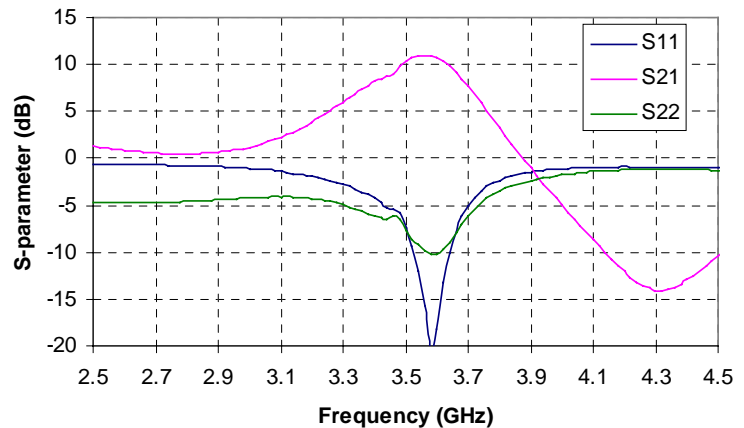
Lead-Free & RoHS compliant.

Evaluation Boards are available.

**TGA2925 Fixture Measured Performance**

Bias Conditions:  $V_d = 8\text{ V}$ ,  $I_{dq} = 0.75\text{ A}$

Performance data taken in a 3.5 GHz application circuit



*Note: This device is early in the characterization process prior to finalizing all electrical specifications. Specifications are subject to change without notice.*

**TABLE I**  
**MAXIMUM RATINGS 1/**

<b>Symbol</b>	<b>Parameter</b>	<b>Value</b>	<b>Notes</b>
V <sub>d</sub>	Drain Supply Voltage	10 V	<u>2/</u>
V <sub>g</sub>	Gate Supply Voltage Range	-0.5 V to -5 V	
I <sub>dq</sub>	Drain Supply Current (Quiescent)	2.1 A	<u>2/</u>
I <sub>g</sub>	Gate Current	30 mA	
P <sub>IN</sub>	Input Continuous Wave Power	35 dBm	<u>2/</u>
P <sub>D</sub>	Power Dissipation	8.2 W	<u>2/</u> , <u>3/</u>
T <sub>CH</sub>	Operating Channel Temperature	175 °C	4/
T <sub>M</sub>	Mounting Temperature (6-10 Seconds)	260 °C	
T <sub>STG</sub>	Storage Temperature	-65 to 150 °C	

- 1/ These ratings represent the maximum operable values for this device.
- 2/ Combinations of supply voltage, supply current, input power, and output power shall not exceed P<sub>D</sub>.
- 3/ When operated at this bias condition with a base plate temperature of 70 °C, the MTTF life is 2E+8 hours.
- 4/ Junction operating temperature will directly affect the device median time to failure (T<sub>M</sub>). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.

**TABLE II**  
**RF CHARACTERIZATION TABLE**  
( $T_A = 25^\circ\text{C}$ , Nominal)  
( $V_d = 8\text{ V}$ ,  $I_{dq} = 0.75\text{ A}$ )

SYMBOL	PARAMETER	TEST CONDITION	TYPICAL	UNITS
Gain	Small Signal Gain	$f = 3.5\text{ GHz}$	11	dB
IRL	Input Return Loss	$f = 3.5\text{ GHz}$	10	dB
ORL	Output Return Loss	$f = 3.5\text{ GHz}$	8	dB
Psat	Saturated Output Power		37.5	dBm

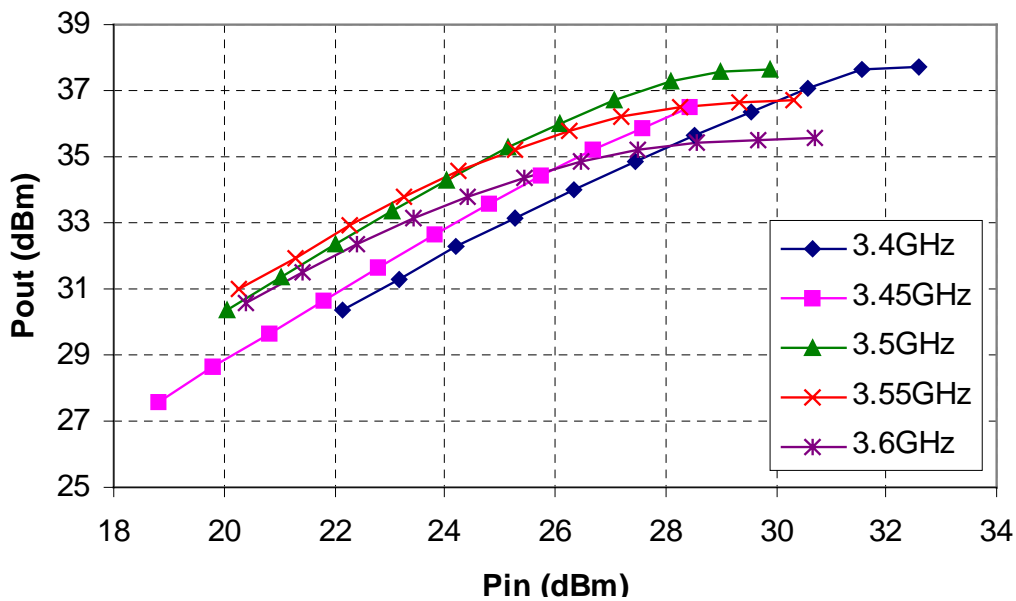
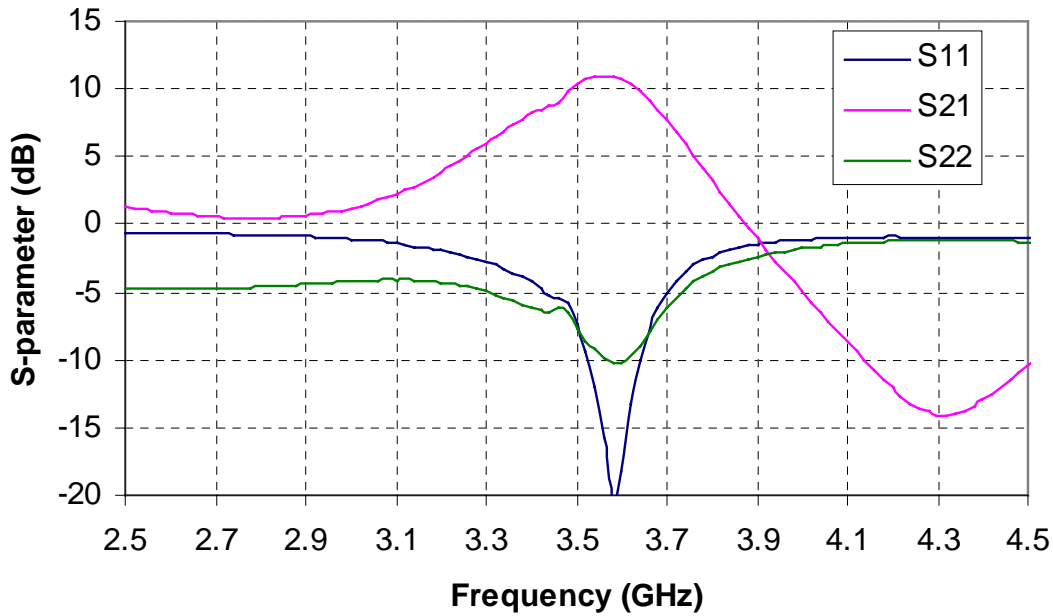
**TABLE III**  
**THERMAL INFORMATION**

Parameter	Test Conditions	$T_{CH}$ ( $^\circ\text{C}$ )	$R_{\theta JC}$ ( $^\circ\text{C/W}$ )	$T_M$ (HRS)
$R_{\theta JC}$ Thermal Resistance (channel to backside of package)	$V_d = 8\text{ V}$ $I_D = 0.75\text{ A}$ $P_{diss} = 6\text{ W}$	143	12.2	1.2E+9

Note: Package backside SnPb soldered to carrier at  $70^\circ\text{C}$  baseplate temperature. At saturated output power, the DC power consumption is 13.2W with 5.6W RF power delivered to the load and 7.6W dissipated.

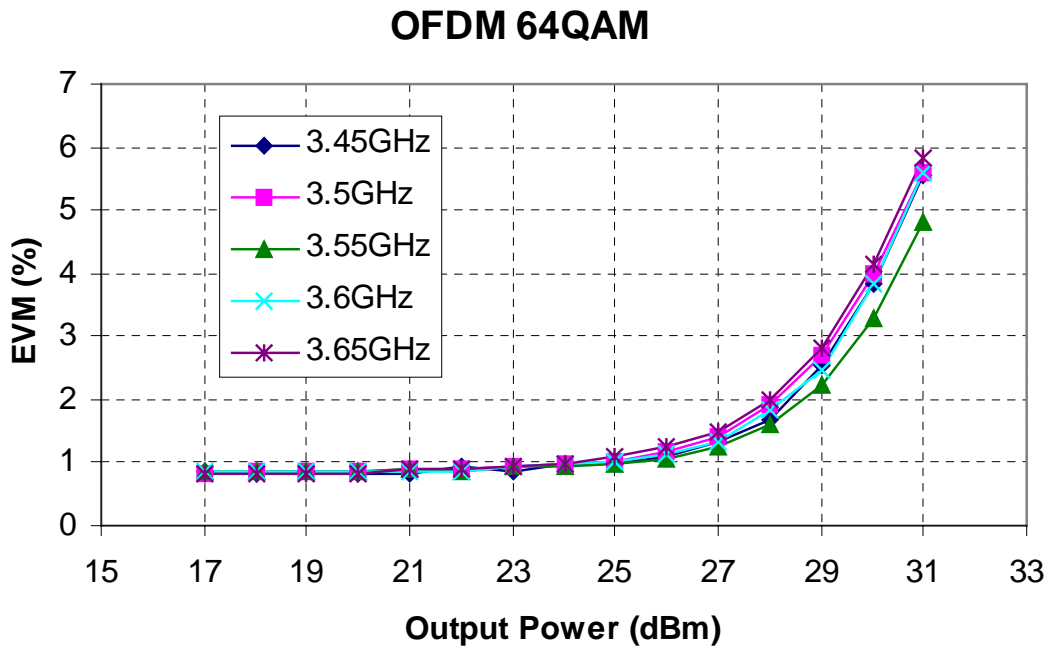
**TGA2925 Measured Fixtured Data  
Application Circuit tuned to 3.5 GHz**

**Bias Conditions:  $V_d = 8\text{ V}$ ,  $I_{dQ} = 0.75\text{ A}$**



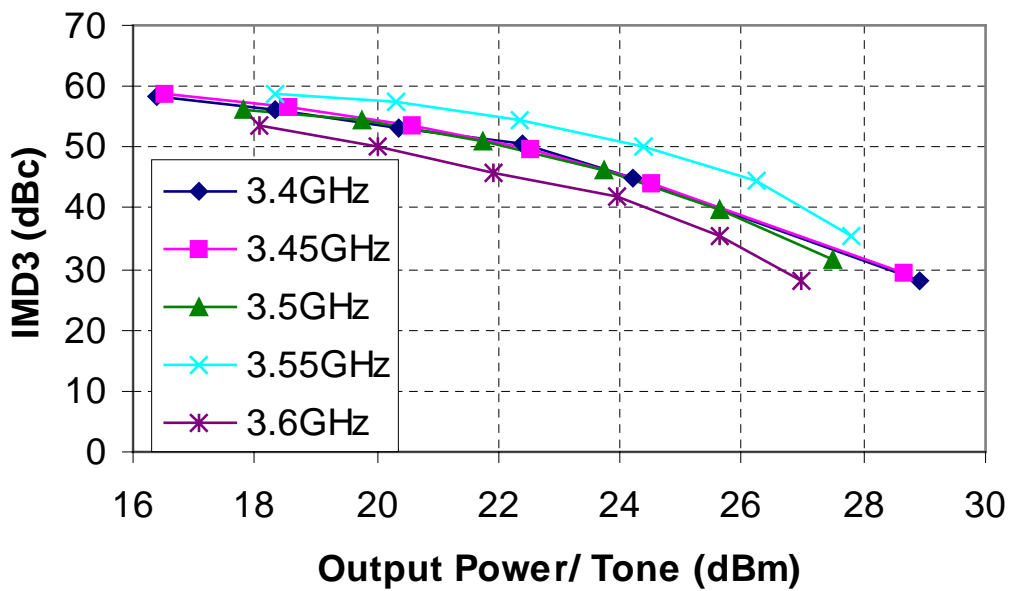
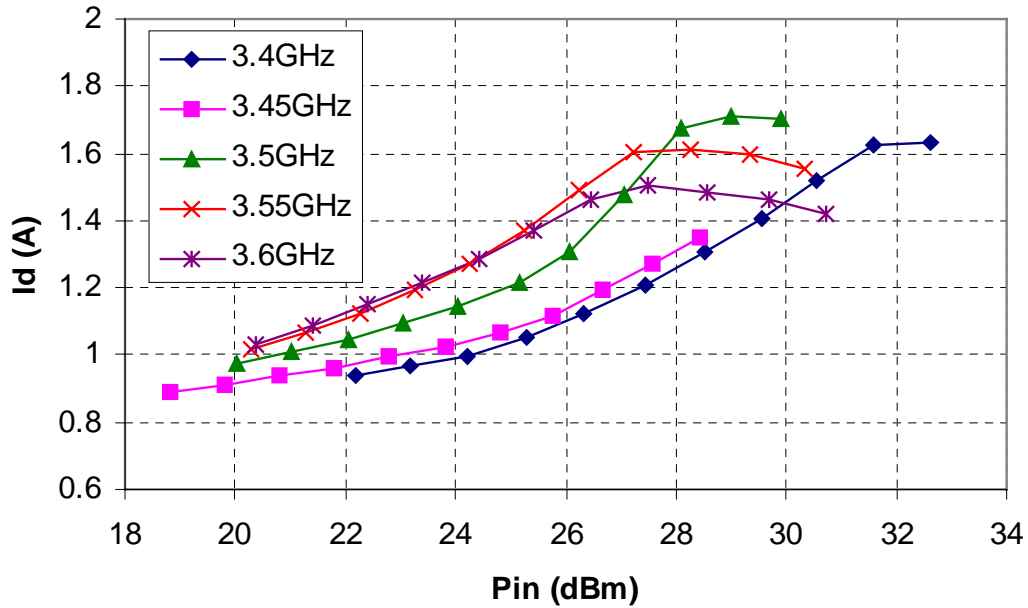
**TGA2925 Measured Fixtured Data**  
**Application Circuit tuned to 3.5 GHz**

**Bias Conditions:  $V_d = 8\text{ V}$ ,  $I_{dq} = 0.75\text{ A}$**

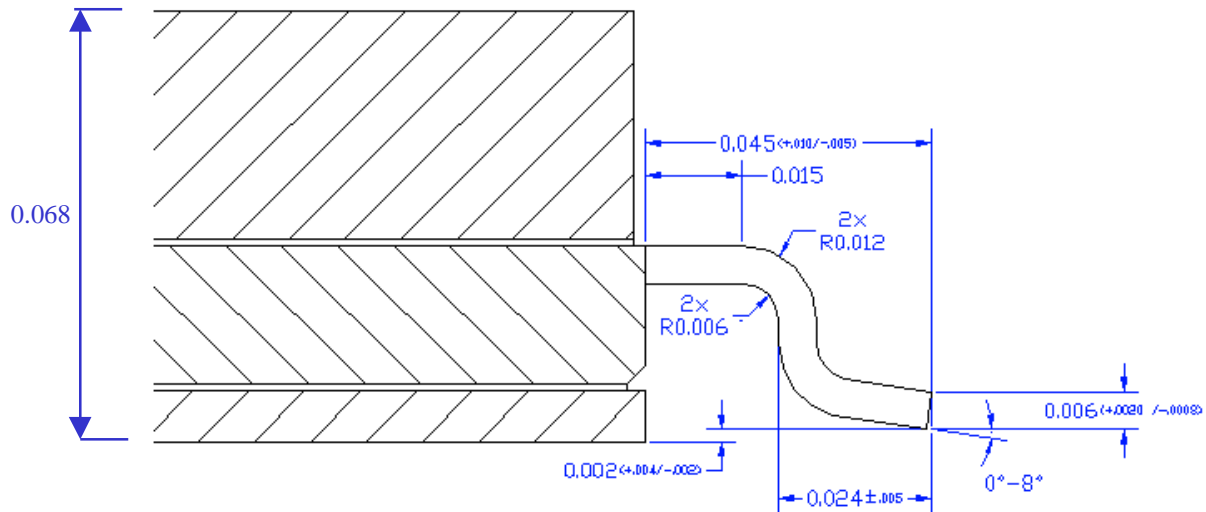
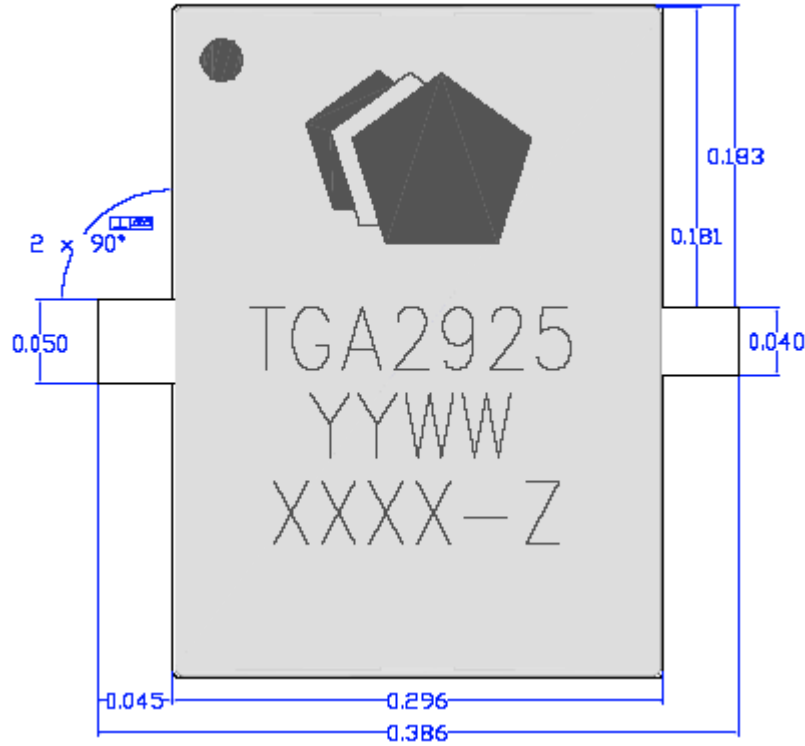


**TGA2925 Measured Fixtured Data  
Application Circuit tuned to 3.5 GHz**

**Bias Conditions:  $V_d = 8\text{ V}$ ,  $I_{dq} = 0.75\text{ A}$**

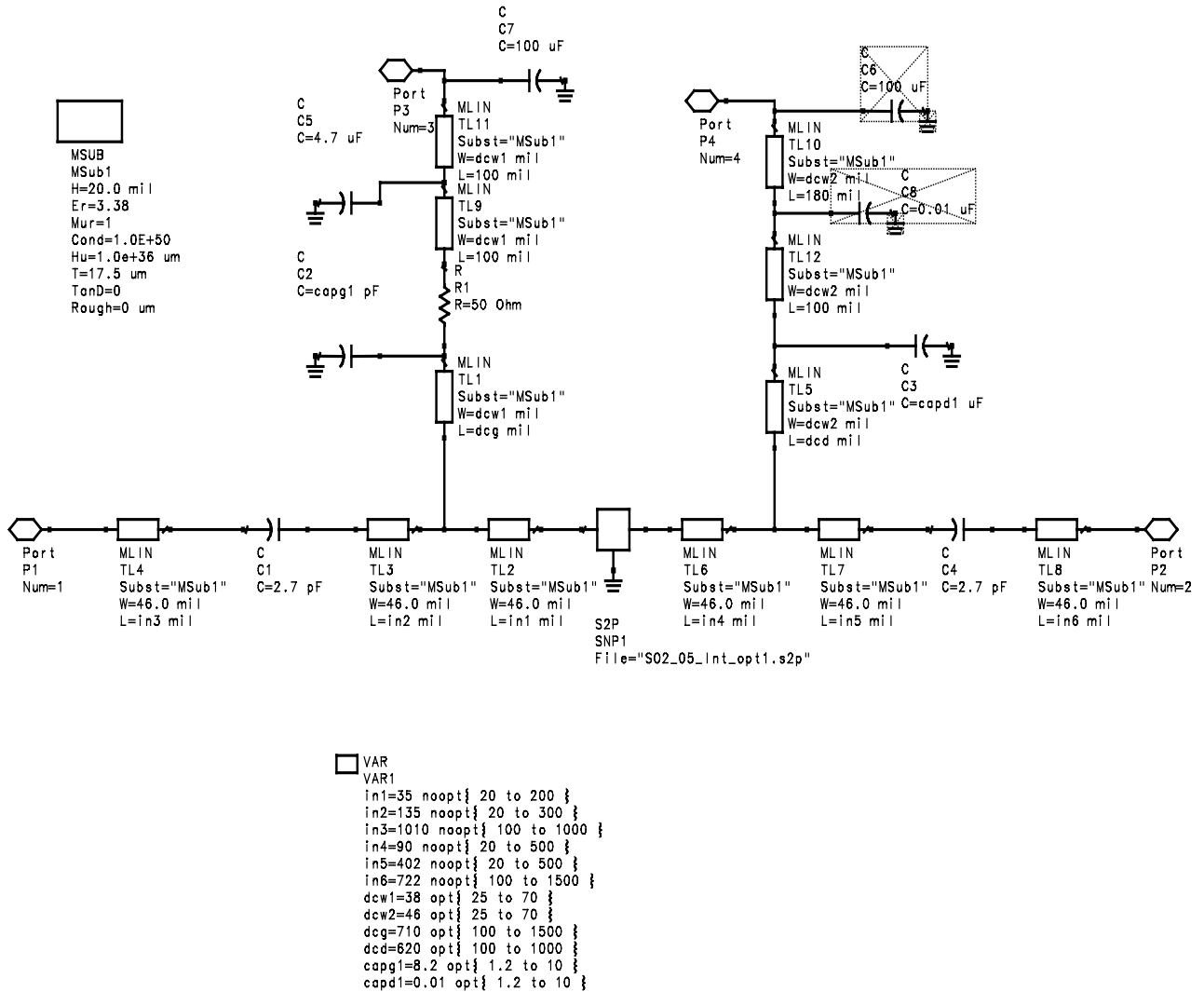


**Mechanical Drawing TGA2925-SG**



Note: All dimensions are in inches with ±5 mil tolerance

### 3.5 GHz Application Circuit Schematic



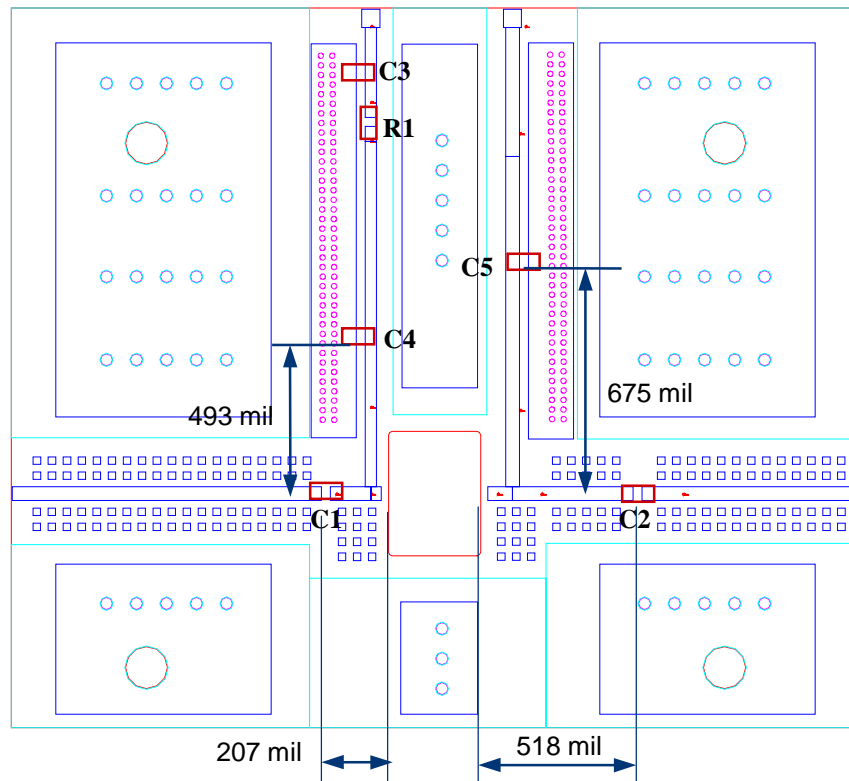
PCB is 20 mil thick Rogers 4003 substrate

#### Bias Procedure

1. Ensure no RF power is applied to the device.
2. Pinch off device by setting  $V_g$  to  $-3V$ .
3. Increase  $V_d$  to 8.0V while monitoring drain current.
4. Increase  $V_g$  until drain current reaches 0.75A
5. Apply RF power.



**Typical Evaluation Board Layout \***



\*The layout is a general purpose drawing that needs to be tuned for the specific application. PCB is RO4003 20 mil thickness, 0.5 oz standard copper cladding, with  $\epsilon_r = 3.38$ .

**External Component Listing**

Part Type	Reference	Description
Capacitor	C1	AVX 06035J5R6BBT, 2.7 pF
Capacitor	C2	AVX 06035J5R6BBT, 2.7 pF
Capacitor	C3	4.7uF
Capacitor	C4	AVX 06035J8R2BBT, 8.2 pF
Capacitor	C5	0.01 uF
Resistor	R1	0805, 50 $\Omega$

**Contact TriQuint Applications Engineering for additional info**

## Recommended Surface Mount Package Assembly

Proper ESD precautions must be followed while handling packages.

Clean the board with acetone. Rinse with alcohol. Allow the circuit to fully dry.

TriQuint recommends using a conductive solder paste for attachment. Follow solder paste and reflow oven vendors' recommendations when developing a solder reflow profile. Typical solder reflow profiles are listed in the table below.

Hand soldering is not recommended. Solder paste can be applied using a stencil printer or dot placement. The volume of solder paste depends on PCB and component layout and should be well controlled to ensure consistent mechanical and electrical performance.

Clean the assembly with alcohol.

## Typical Solder Reflow Profiles

Reflow Profile	SnPb	Pb Free
Ramp-up Rate	3 °C/sec	3 °C/sec
Activation Time and Temperature	60 – 120 sec @ 140 – 160 °C	60 – 180 sec @ 150 – 200 °C
Time above Melting Point	60 – 150 sec	60 – 150 sec
Max Peak Temperature	240 °C	260 °C
Time within 5 °C of Peak Temperature	10 – 20 sec	10 – 20 sec
Ramp-down Rate	4 – 6 °C/sec	4 – 6 °C/sec

## Ordering Information

Part	Package Style
TGA2925-SG	Gull Wing Leads